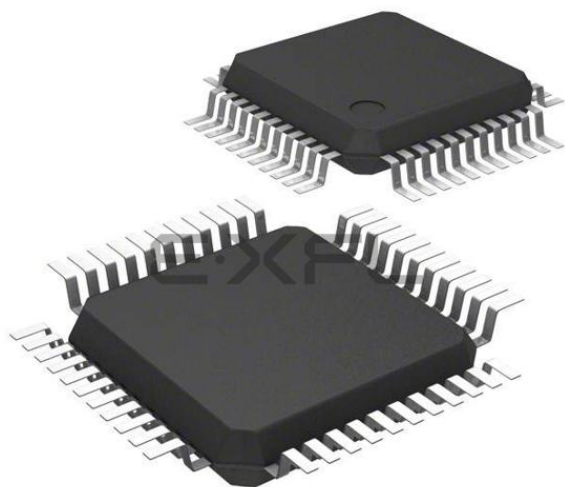




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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	31
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 10x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	44-LQFP
Supplier Device Package	44-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100fcdfp-v0

Table 1-1. List of Ordering Part Numbers

(2/12)

Pin count	Package	Data flash	Fields of Application Note	Ordering Part Number
25 pins	25-pin plastic WFLGA (3 × 3 mm, 0.5 mm pitch)	Mounted	A G	R5F1008AALA#U0, R5F1008CALA#U0, R5F1008DALA#U0, R5F1008EALA#U0 R5F1008AALA#W0, R5F1008CALA#W0, R5F1008DALA#W0, R5F1008EALA#W0 R5F1008AGLA#U0, R5F1008CGLA#U0, R5F1008DGLA#U0, R5F1008EGLA#U0 R5F1008AGLA#W0, R5F1008CGLA#W0, R5F1008DGLA#W0, R5F1008EGLA#W0
		Not mounted	A	R5F1018AALA#U0, R5F1018CALA#U0, R5F1018DALA#U0, R5F1018EALA#U0 R5F1018AALA#W0, R5F1018CALA#W0, R5F1018DALA#W0, R5F1018EALA#W0
30 pins	30-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)	Mounted	A D G	R5F100AAASP#V0, R5F100ACASP#V0, R5F100ADASP#V0, R5F100AEASP#V0, R5F100AFASP#V0, R5F100AGASP#V0 R5F100AAASP#X0, R5F100ACASP#X0, R5F100ADASP#X0, R5F100AEASP#X0, R5F100AFASP#X0, R5F100AGASP#X0 R5F100AADSP#V0, R5F100ACDSP#V0, R5F100ADDSP#V0, R5F100AEDSP#V0, R5F100AFDSP#V0, R5F100AGDSP#V0 R5F100AADSP#X0, R5F100ACDSP#X0, R5F100ADDSP#X0, R5F100AEDSP#X0, R5F100AFDSP#X0, R5F100AGDSP#X0 R5F100AAGSP#V0, R5F100ACGSP#V0, R5F100ADGSP#V0, R5F100AEGSP#V0, R5F100AFGSP#V0, R5F100AGGSP#V0 R5F100AAGSP#X0, R5F100ACGSP#X0, R5F100ADGSP#X0, R5F100AEGSP#X0, R5F100AFGSP#X0, R5F100AGGSP#X0
		Not mounted	A D	R5F101AAASP#V0, R5F101ACASP#V0, R5F101ADASP#V0, R5F101AEASP#V0, R5F101AFASP#V0, R5F101AGASP#V0 R5F101AAASP#X0, R5F101ACASP#X0, R5F101ADASP#X0, R5F101AEASP#X0, R5F101AFASP#X0, R5F101AGASP#X0 R5F101AADSP#V0, R5F101ACDSP#V0, R5F101ADDSP#V0, R5F101AEDSP#V0, R5F101AFDSP#V0, R5F101AGDSP#V0 R5F101AADSP#X0, R5F101ACDSP#X0, R5F101ADDSP#X0, R5F101AEDSP#X0, R5F101AFDSP#X0, R5F101AGDSP#X0
32 pins	32-pin plastic HWQFN (5 × 5 mm, 0.5 mm pitch)	Mounted	A D G	R5F100BAANA#U0, R5F100BCANA#U0, R5F100BDANA#U0, R5F100BEANA#U0, R5F100BFANA#U0, R5F100BGANA#U0 R5F100BAANA#W0, R5F100BCANA#W0, R5F100BDANA#W0, R5F100BEANA#W0, R5F100BFANA#W0, R5F100BGANA#W0 R5F100BADNA#U0, R5F100BCDNA#U0, R5F100BDDNA#U0, R5F100BEDNA#U0, R5F100BFDNA#U0, R5F100BGDNA#U0 R5F100BADNA#W0, R5F100BCDNA#W0, R5F100BDDNA#W0, R5F100BEDNA#W0, R5F100BFDNA#W0, R5F100BGDNA#W0 R5F100BAGNA#U0, R5F100BCGNA#U0, R5F100BDGNA#U0, R5F100BEGNA#U0, R5F100BFGNA#U0, R5F100BGGNA#U0 R5F100BAGNA#W0, R5F100BCGNA#W0, R5F100BDGNA#W0, R5F100BEGNA#W0, R5F100BFGNA#W0, R5F100BGGNA#W0
		Not mounted	A D	R5F101BAANA#U0, R5F101BCANA#U0, R5F101BDANA#U0, R5F101BEANA#U0, R5F101BFANA#U0, R5F101BGANA#U0 R5F101BAANA#W0, R5F101BCANA#W0, R5F101BDANA#W0, R5F101BEANA#W0, R5F101BFANA#W0, R5F101BGANA#W0 R5F101BADNA#U0, R5F101BCDNA#U0, R5F101BDDNA#U0, R5F101BEDNA#U0, R5F101BFDNA#U0, R5F101BGDNA#U0 R5F101BADNA#W0, R5F101BCDNA#W0, R5F101BDDNA#W0, R5F101BEDNA#W0, R5F101BFDNA#W0, R5F101BGDNA#W0

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

Table 1-1. List of Ordering Part Numbers

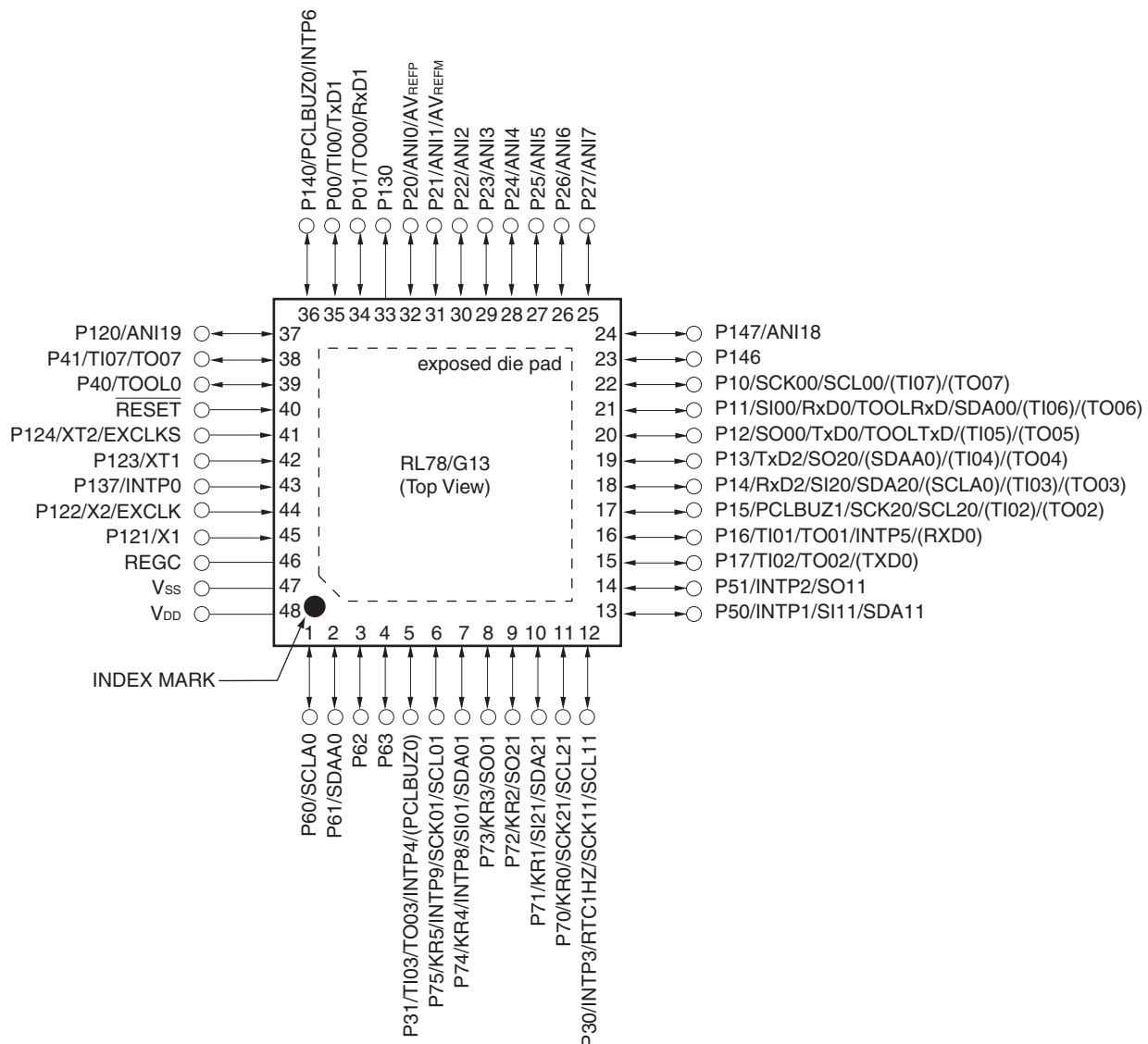
(6/12)

Pin count	Package	Data flash	Fields of Application Note	Ordering Part Number
48 pins	48-pin plastic HWQFN (7 × 7 mm, 0.5 mm pitch)	Mounted	A	R5F100GAANA#U0, R5F100GCANA#U0, R5F100GDANA#U0, R5F100GEANA#U0, R5F100GFANA#U0, R5F100GGANA#U0, R5F100GHANA#U0, R5F100GJANA#U0, R5F100GKANA#U0, R5F100GLANA#U0 R5F100GAANA#W0, R5F100GCANA#W0, R5F100GDANA#W0, R5F100GEANA#W0, R5F100GFANA#W0, R5F100GGANA#W0, R5F100GHANA#W0, R5F100GJANA#W0, R5F100GKANA#W0, R5F100GLANA#W0
		Not mounted	D	R5F100GADNA#U0, R5F100GCDNA#U0, R5F100GDDNA#U0, R5F100GEDNA#U0, R5F100GFDNA#U0, R5F100GGDNA#U0, R5F100GHDNA#U0, R5F100GJDNA#U0, R5F100GKDNA#U0, R5F100GLDNA#U0 R5F100GADNA#W0, R5F100GCDNA#W0, R5F100GDDNA#W0, R5F100GEDNA#W0, R5F100GFDNA#W0, R5F100GGDNA#W0, R5F100GHDNA#W0, R5F100GJDNA#W0, R5F100GKDNA#W0, R5F100GLDNA#W0
			G	R5F100GAGNA#U0, R5F100GCGNA#U0, R5F100GDGNA#U0, R5F100GEGNA#U0, R5F100GFGNA#U0, R5F100GGGNA#U0, R5F100GHGNA#U0, R5F100GJGNA#U0 R5F100GAGNA#W0, R5F100GCGNA#W0, R5F100GDGNA#W0, R5F100GEGNA#W0, R5F100GFGNA#W0, R5F100GGGNA#W0, R5F100GHGNA#W0, R5F100GJGNA#W0
			A	R5F101GAANA#U0, R5F101GCANA#U0, R5F101GDANA#U0, R5F101GEANA#U0, R5F101GFANA#U0, R5F101GGANA#U0, R5F101GHANA#U0, R5F101GJANA#U0, R5F101GKANA#U0, R5F101GLANA#U0 R5F101GAANA#W0, R5F101GCANA#W0, R5F101GDANA#W0, R5F101GEANA#W0, R5F101GFANA#W0, R5F101GGANA#W0, R5F101GHANA#W0, R5F101GJANA#W0, R5F101GKANA#W0, R5F101GLANA#W0
			D	R5F101GADNA#U0, R5F101GCDNA#U0, R5F101GDDNA#U0, R5F101GEDNA#U0, R5F101GFDNA#U0, R5F101GGDNA#U0, R5F101GHDNA#U0, R5F101GJDNA#U0, R5F101GKDNA#U0, R5F101GLDNA#U0 R5F101GADNA#W0, R5F101GCDNA#W0, R5F101GDDNA#W0, R5F101GEDNA#W0, R5F101GFDNA#W0, R5F101GGDNA#W0, R5F101GHDNA#W0, R5F101GJDNA#W0, R5F101GKDNA#W0, R5F101GLDNA#W0

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

- 48-pin plastic HWQFN (7 × 7 mm, 0.5 mm pitch)



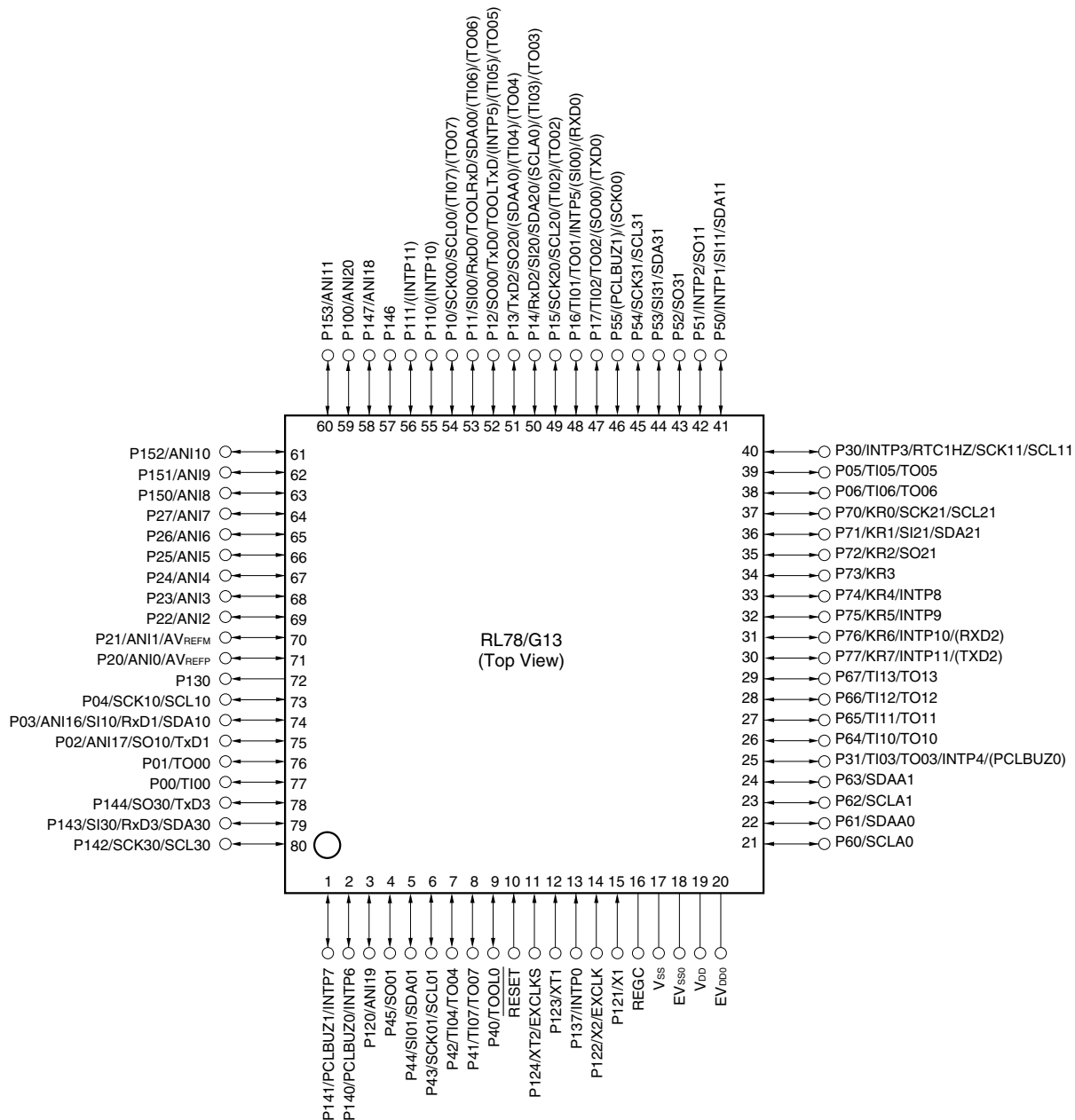
Caution Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

- Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.
- It is recommended to connect an exposed die pad to V_{SS}.

1.3.12 80-pin products

- 80-pin plastic LQFP (14 × 14 mm, 0.65 mm pitch)
- 80-pin plastic LFQFP (12 × 12 mm, 0.5 mm pitch)

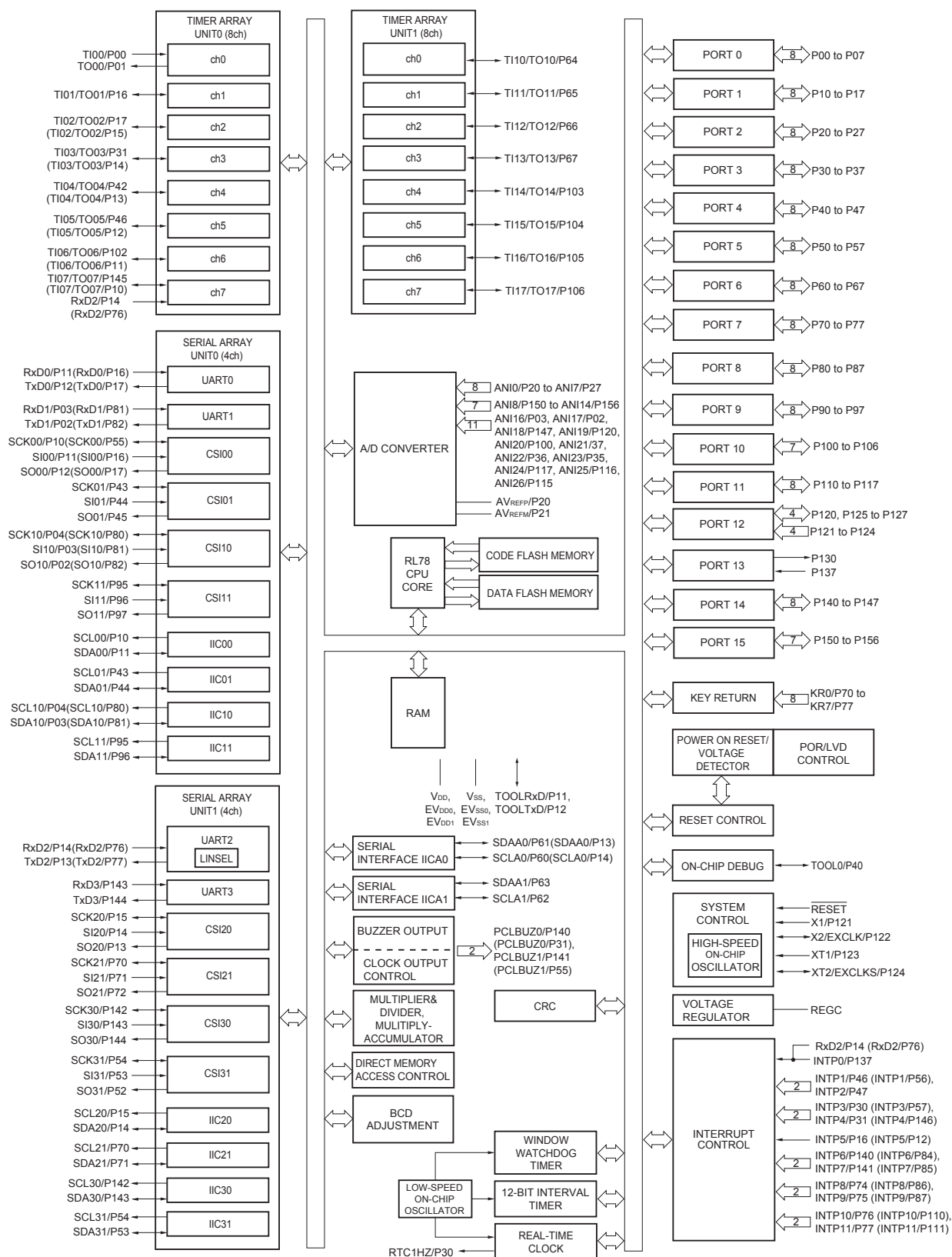


- Cautions**
1. Make EV_{SS0} pin the same potential as V_{SS} pin.
 2. Make V_{DD} pin the potential that is higher than EV_{DD0} pin.
 3. Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD} and EV_{DD0} pins and connect the V_{SS} and EV_{SS0} pins to separate ground lines.
3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.5.14 128-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

[80-pin, 100-pin, 128-pin products]

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

(1/2)

Item		80-pin		100-pin		128-pin	
		R5F100Mx	R5F101Mx	R5F100Px	R5F101Px	R5F100Sx	R5F101Sx
Code flash memory (KB)		96 to 512		96 to 512		192 to 512	
Data flash memory (KB)		8	—	8	—	8	—
RAM (KB)		8 to 32 ^{Note 1}		8 to 32 ^{Note 1}		16 to 32 ^{Note 1}	
Address space		1 MB					
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (High-speed main) mode: 1 to 20 MHz (V _{DD} = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V _{DD} = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V _{DD} = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V _{DD} = 1.6 to 5.5 V)					
	High-speed on-chip oscillator	HS (High-speed main) mode: 1 to 32 MHz (V _{DD} = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V _{DD} = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V _{DD} = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V _{DD} = 1.6 to 5.5 V)					
Subsystem clock		XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz					
Low-speed on-chip oscillator		15 kHz (TYP.)					
General-purpose register		(8-bit register × 8) × 4 banks					
Minimum instruction execution time		0.03125 μs (High-speed on-chip oscillator: f _{IH} = 32 MHz operation)					
		0.05 μs (High-speed system clock: f _{MX} = 20 MHz operation)					
		30.5 μs (Subsystem clock: f _{SUB} = 32.768 kHz operation)					
Instruction set		• Data transfer (8/16 bits) • Adder and subtractor/logical operation (8/16 bits) • Multiplication (8 bits × 8 bits) • Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.					
I/O port	Total	74		92		120	
	CMOS I/O	64 (N-ch O.D. I/O [EV _{DD} withstand voltage]: 21)		82 (N-ch O.D. I/O [EV _{DD} withstand voltage]: 24)		110 (N-ch O.D. I/O [EV _{DD} withstand voltage]: 25)	
	CMOS input	5		5		5	
	CMOS output	1		1		1	
	N-ch O.D. I/O (withstand voltage: 6 V)	4		4		4	
Timer	16-bit timer	12 channels		12 channels		16 channels	
	Watchdog timer	1 channel		1 channel		1 channel	
	Real-time clock (RTC)	1 channel		1 channel		1 channel	
	12-bit interval timer (IT)	1 channel		1 channel		1 channel	
	Timer output	12 channels (PWM outputs: 10 ^{Note 2})		12 channels (PWM outputs: 10 ^{Note 2})		16 channels (PWM outputs: 14 ^{Note 2})	
	RTC output	1 channel • 1 Hz (subsystem clock: f _{SUB} = 32.768 kHz)					

Notes 1. The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xJ, R5F101xJ (x = M, P): Start address FAF00H

R5F100xL, R5F101xL (x = M, P, S): Start address F7F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (3/5)

Items	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input voltage, high	V _{IH1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	Normal input buffer	0.8EV _{DD0}	EV _{DD0}	V
	V _{IH2}	P01, P03, P04, P10, P11, P13 to P17, P43, P44, P53 to P55, P80, P81, P142, P143	TTL input buffer 4.0 V ≤ EV _{DD0} ≤ 5.5 V	2.2	EV _{DD0}	V
			TTL input buffer 3.3 V ≤ EV _{DD0} < 4.0 V	2.0	EV _{DD0}	V
			TTL input buffer 1.6 V ≤ EV _{DD0} < 3.3 V	1.5	EV _{DD0}	V
	V _{IH3}	P20 to P27, P150 to P156	0.7V _{DD}		V _{DD}	V
	V _{IH4}	P60 to P63	0.7EV _{DD0}		6.0	V
	V _{IH5}	P121 to P124, P137, EXCLK, EXCLKS, RESET	0.8V _{DD}		V _{DD}	V
Input voltage, low	V _{IL1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	Normal input buffer	0	0.2EV _{DD0}	V
	V _{IL2}	P01, P03, P04, P10, P11, P13 to P17, P43, P44, P53 to P55, P80, P81, P142, P143	TTL input buffer 4.0 V ≤ EV _{DD0} ≤ 5.5 V	0	0.8	V
			TTL input buffer 3.3 V ≤ EV _{DD0} < 4.0 V	0	0.5	V
			TTL input buffer 1.6 V ≤ EV _{DD0} < 3.3 V	0	0.32	V
	V _{IL3}	P20 to P27, P150 to P156	0		0.3V _{DD}	V
	V _{IL4}	P60 to P63	0		0.3EV _{DD0}	V
	V _{IL5}	P121 to P124, P137, EXCLK, EXCLKS, RESET	0		0.2V _{DD}	V

Caution The maximum value of V_{IH} of pins P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 is EV_{DD0}, even in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2.3.2 Supply current characteristics

(1) Flash ROM: 16 to 64 KB of 20- to 64-pin products

(T_A = -40 to +85°C, 1.6 V ≤ E_{VDD0} ≤ V_{DD} ≤ 5.5 V, V_{SS} = E_{VSS0} = 0 V) (1/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit		
Supply current ^{Note 1}	I _{DD1}	Operating mode	HS (high-speed main) mode ^{Note 5}	f _{IH} = 32 MHz ^{Note 3}	Basic operation	V _{DD} = 5.0 V		2.1		mA	
						V _{DD} = 3.0 V		2.1		mA	
					Normal operation	V _{DD} = 5.0 V		4.6	7.0	mA	
						V _{DD} = 3.0 V		4.6	7.0	mA	
				f _{IH} = 24 MHz ^{Note 3}	Normal operation	V _{DD} = 5.0 V		3.7	5.5	mA	
						V _{DD} = 3.0 V		3.7	5.5	mA	
				f _{IH} = 16 MHz ^{Note 3}	Normal operation	V _{DD} = 5.0 V		2.7	4.0	mA	
						V _{DD} = 3.0 V		2.7	4.0	mA	
				LS (low-speed main) mode ^{Note 5}	f _{IH} = 8 MHz ^{Note 3}	Normal operation	V _{DD} = 3.0 V		1.2	1.8	mA
							V _{DD} = 2.0 V		1.2	1.8	mA
				LV (low-voltage main) mode ^{Note 5}	f _{IH} = 4 MHz ^{Note 3}	Normal operation	V _{DD} = 3.0 V		1.2	1.7	mA
							V _{DD} = 2.0 V		1.2	1.7	mA
			HS (high-speed main) mode ^{Note 5}	f _{MX} = 20 MHz ^{Note 2} , V _{DD} = 5.0 V	Normal operation	Square wave input		3.0	4.6	mA	
						Resonator connection		3.2	4.8	mA	
					Normal operation	Square wave input		3.0	4.6	mA	
						Resonator connection		3.2	4.8	mA	
					f _{MX} = 10 MHz ^{Note 2} , V _{DD} = 5.0 V	Normal operation	Square wave input		1.9	2.7	mA
							Resonator connection		1.9	2.7	mA
					f _{MX} = 10 MHz ^{Note 2} , V _{DD} = 3.0 V	Normal operation	Square wave input		1.9	2.7	mA
							Resonator connection		1.9	2.7	mA
				LS (low-speed main) mode ^{Note 5}	f _{MX} = 8 MHz ^{Note 2} , V _{DD} = 3.0 V	Normal operation	Square wave input		1.1	1.7	mA
							Resonator connection		1.1	1.7	mA
					f _{MX} = 8 MHz ^{Note 2} , V _{DD} = 2.0 V	Normal operation	Square wave input		1.1	1.7	mA
							Resonator connection		1.1	1.7	mA
			Subsystem clock operation	f _{SUB} = 32.768 kHz ^{Note 4} T _A = −40°C	Normal operation	Square wave input		4.1	4.9	μA	
						Resonator connection		4.2	5.0	μA	
				f _{SUB} = 32.768 kHz ^{Note 4} T _A = +25°C	Normal operation	Square wave input		4.1	4.9	μA	
						Resonator connection		4.2	5.0	μA	
				f _{SUB} = 32.768 kHz ^{Note 4} T _A = +50°C	Normal operation	Square wave input		4.2	5.5	μA	
						Resonator connection		4.3	5.6	μA	
				f _{SUB} = 32.768 kHz ^{Note 4} T _A = +70°C	Normal operation	Square wave input		4.3	6.3	μA	
						Resonator connection		4.4	6.4	μA	
				f _{SUB} = 32.768 kHz ^{Note 4} T _A = +85°C	Normal operation	Square wave input		4.6	7.7	μA	
						Resonator connection		4.7	7.8	μA	

(Notes and Remarks are listed on the next page.)

- Notes**
1. Total current flowing into V_{DD} and EV_{DD0} , including the input leakage current flowing when the level of the input pin is fixed to V_{DD} , EV_{DD0} or V_{SS} , EV_{SS0} . The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 2. During HALT instruction execution by flash memory.
 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 4. When high-speed system clock and subsystem clock are stopped.
 5. When high-speed on-chip oscillator and high-speed system clock are stopped. When $RTCLPC = 1$ and setting ultra-low current consumption ($AMPHS1 = 1$). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
HS (high-speed main) mode: $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$ @ 1 MHz to 32 MHz
 $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$ @ 1 MHz to 16 MHz
LS (low-speed main) mode: $1.8\text{ V} \leq V_{DD} \leq 5.5\text{ V}$ @ 1 MHz to 8 MHz
LV (low-voltage main) mode: $1.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$ @ 1 MHz to 4 MHz
 8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.

- Remarks 1.** f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
2. f_{IH}: High-speed on-chip oscillator clock frequency
3. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)
4. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is T_A = 25°C

- Notes**
1. Total current flowing into V_{DD}, EV_{DD0}, and EV_{DD1}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, EV_{DD0}, and EV_{DD1}, or V_{SS}, EV_{SS0}, and EV_{SS1}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 3. When high-speed system clock and subsystem clock are stopped.
 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
 - HS (high-speed main) mode: $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$ @ 1 MHz to 32 MHz
 - $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$ @ 1 MHz to 16 MHz
 - LS (low-speed main) mode: $1.8\text{ V} \leq V_{DD} \leq 5.5\text{ V}$ @ 1 MHz to 8 MHz
 - LV (low-voltage main) mode: $1.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$ @ 1 MHz to 4 MHz

- Remarks**
1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 2. f_{IH}: High-speed on-chip oscillator clock frequency
 3. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)
 4. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C

2.4 AC Characteristics

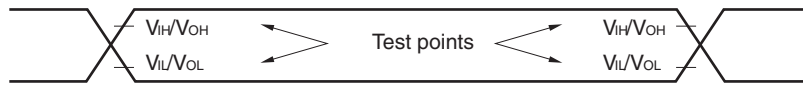
(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	T _{CY}	Main system clock (f _{MAIN}) operation	HS (high-speed main) mode	2.7 V ≤ V _{DD} ≤ 5.5 V	0.03125	1	μs
				2.4 V ≤ V _{DD} < 2.7 V	0.0625	1	μs
			LS (low-speed main) mode	1.8 V ≤ V _{DD} ≤ 5.5 V	0.125	1	μs
			LV (low-voltage main) mode	1.6 V ≤ V _{DD} ≤ 5.5 V	0.25	1	μs
		Subsystem clock (f _{SUB}) operation		1.8 V ≤ V _{DD} ≤ 5.5 V	28.5	30.5	31.3 μs
		In the self programming mode	HS (high-speed main) mode	2.7 V ≤ V _{DD} ≤ 5.5 V	0.03125	1	μs
				2.4 V ≤ V _{DD} < 2.7 V	0.0625	1	μs
			LS (low-speed main) mode	1.8 V ≤ V _{DD} ≤ 5.5 V	0.125	1	μs
			LV (low-voltage main) mode	1.8 V ≤ V _{DD} ≤ 5.5 V	0.25	1	μs
External system clock frequency	f _{EX}	2.7 V ≤ V _{DD} ≤ 5.5 V		1.0		20.0	MHz
		2.4 V ≤ V _{DD} < 2.7 V		1.0		16.0	MHz
		1.8 V ≤ V _{DD} < 2.4 V		1.0		8.0	MHz
		1.6 V ≤ V _{DD} < 1.8 V		1.0		4.0	MHz
	f _{EXS}			32		35	kHz
External system clock input high-level width, low-level width	t _{EXH} , t _{EXL}	2.7 V ≤ V _{DD} ≤ 5.5 V		24			ns
		2.4 V ≤ V _{DD} < 2.7 V		30			ns
		1.8 V ≤ V _{DD} < 2.4 V		60			ns
		1.6 V ≤ V _{DD} < 1.8 V		120			ns
	t _{EXHS} , t _{EXLS}			13.7			μs
Ti00 to Ti07, Ti10 to Ti17 input high-level width, low-level width	t _{TIH} , t _{TIL}			1/f _{MCK} +10			ns ^{Note}
TO00 to TO07, TO10 to TO17 output frequency	f _{TO}	HS (high-speed main) mode		4.0 V ≤ EV _{DD0} ≤ 5.5 V		16	MHz
				2.7 V ≤ EV _{DD0} < 4.0 V		8	MHz
				1.8 V ≤ EV _{DD0} < 2.7 V		4	MHz
				1.6 V ≤ EV _{DD0} < 1.8 V		2	MHz
		LS (low-speed main) mode		1.8 V ≤ EV _{DD0} ≤ 5.5 V		4	MHz
				1.6 V ≤ EV _{DD0} < 1.8 V		2	MHz
		LV (low-voltage main) mode		1.6 V ≤ EV _{DD0} ≤ 5.5 V		2	MHz
PCLBUZ0, PCLBUZ1 output frequency	f _{PCL}	HS (high-speed main) mode		4.0 V ≤ EV _{DD0} ≤ 5.5 V		16	MHz
				2.7 V ≤ EV _{DD0} < 4.0 V		8	MHz
				1.8 V ≤ EV _{DD0} < 2.7 V		4	MHz
				1.6 V ≤ EV _{DD0} < 1.8 V		2	MHz
		LS (low-speed main) mode		1.8 V ≤ EV _{DD0} ≤ 5.5 V		4	MHz
				1.6 V ≤ EV _{DD0} < 1.8 V		2	MHz
		LV (low-voltage main) mode		1.8 V ≤ EV _{DD0} ≤ 5.5 V		4	MHz
				1.6 V ≤ EV _{DD0} < 1.8 V		2	MHz
Interrupt input high-level width, low-level width	t _{INTH} , t _{INTL}	INTP0		1.6 V ≤ V _{DD} ≤ 5.5 V	1		μs
		INTP1 to INTP11		1.6 V ≤ EV _{DD0} ≤ 5.5 V	1		μs
Key interrupt input low-level width	t _{KR}	KR0 to KR7		1.8 V ≤ EV _{DD0} ≤ 5.5 V	250		ns
				1.6 V ≤ EV _{DD0} < 1.8 V	1		μs
RESET low-level width	t _{RSL}			10			μs

(Note and Remark are listed on the next page.)

2.5 Peripheral Functions Characteristics

AC Timing Test Points



2.5.1 Serial array unit

(1) During communication at same potential (UART mode)

(T_A = -40 to +85°C, 1.6 V ≤ E_{VDD0} = E_{VDD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = E_{VSS0} = E_{VSS1} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate ^{Note 1}		2.4 V ≤ E _{VDD0} ≤ 5.5 V		f _{MCK} /6 ^{Note 2}		f _{MCK} /6		f _{MCK} /6	bps
		Theoretical value of the maximum transfer rate f _{MCK} = f _{CLK} ^{Note 3}		5.3		1.3		0.6	Mbps
		1.8 V ≤ E _{VDD0} ≤ 5.5 V		f _{MCK} /6 ^{Note 2}		f _{MCK} /6		f _{MCK} /6	bps
		Theoretical value of the maximum transfer rate f _{MCK} = f _{CLK} ^{Note 3}		5.3		1.3		0.6	Mbps
		1.7 V ≤ E _{VDD0} ≤ 5.5 V		f _{MCK} /6 ^{Note 2}		f _{MCK} /6 ^{Note 2}		f _{MCK} /6	bps
		Theoretical value of the maximum transfer rate f _{MCK} = f _{CLK} ^{Note 3}		5.3		1.3		0.6	Mbps
		1.6 V ≤ E _{VDD0} ≤ 5.5 V	—			f _{MCK} /6 ^{Note 2}		f _{MCK} /6	bps
		Theoretical value of the maximum transfer rate f _{MCK} = f _{CLK} ^{Note 3}	—			1.3		0.6	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. The following conditions are required for low voltage interface when E_{VDD0} < V_{DD}.

2.4 V ≤ E_{VDD0} < 2.7 V : MAX. 2.6 Mbps

1.8 V ≤ E_{VDD0} < 2.4 V : MAX. 1.3 Mbps

1.6 V ≤ E_{VDD0} < 1.8 V : MAX. 0.6 Mbps

3. The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:

HS (high-speed main) mode: 32 MHz (2.7 V ≤ V_{DD} ≤ 5.5 V)

16 MHz (2.4 V ≤ V_{DD} ≤ 5.5 V)

LS (low-speed main) mode: 8 MHz (1.8 V ≤ V_{DD} ≤ 5.5 V)

LV (low-voltage main) mode: 4 MHz (1.6 V ≤ V_{DD} ≤ 5.5 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)**(T_A = -40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (2/2)**

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp high-/low-level width	t _{KH2} , t _{KL2}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V	t _{KCY2} /2 - 12		t _{KCY2} /2 - 50		t _{KCY2} /2 - 50		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V	t _{KCY2} /2 - 18		t _{KCY2} /2 - 50		t _{KCY2} /2 - 50		ns
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 2}	t _{KCY2} /2 - 50		t _{KCY2} /2 - 50		t _{KCY2} /2 - 50		ns
Slp setup time (to SCKp↑) ^{Note 3}	t _{SIK2}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V	1/f _{MCK} + 20		1/f _{MCK} + 30		1/f _{MCK} + 30		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V	1/f _{MCK} + 20		1/f _{MCK} + 30		1/f _{MCK} + 30		ns
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 2}	1/f _{MCK} + 30		1/f _{MCK} + 30		1/f _{MCK} + 30		ns
Slp hold time (from SCKp↑) ^{Note 4}	t _{KS12}		1/f _{MCK} + 31		1/f _{MCK} + 31		1/f _{MCK} + 31		ns
Delay time from SCKp↓ to SOp output ^{Note 5}	t _{KSO2}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ		2/f _{MCK} + 120		2/f _{MCK} + 573		2/f _{MCK} + 573	ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ		2/f _{MCK} + 214		2/f _{MCK} + 573		2/f _{MCK} + 573	ns
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 2} , C _b = 30 pF, R _b = 5.5 kΩ		2/f _{MCK} + 573		2/f _{MCK} + 573		2/f _{MCK} + 573	ns

Notes 1. Transfer rate in the SNOOZE mode : MAX. 1 Mbps2. Use it with EV_{DD0} ≥ V_b.

3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

5. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the Slp pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

(2) I²C fast mode**(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)**

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	f _{SCL}	Fast mode: f _{CLK} ≥ 3.5 MHz	2.7 V ≤ EV _{DD0} ≤ 5.5 V	0	400	0	400	0	400	kHz
			1.8 V ≤ EV _{DD0} ≤ 5.5 V	0	400	0	400	0	400	kHz
Setup time of restart condition	t _{SU:STA}	2.7 V ≤ EV _{DD0} ≤ 5.5 V		0.6		0.6		0.6		μs
		1.8 V ≤ EV _{DD0} ≤ 5.5 V		0.6		0.6		0.6		μs
Hold time ^{Note 1}	t _{HD:STA}	2.7 V ≤ EV _{DD0} ≤ 5.5 V		0.6		0.6		0.6		μs
		1.8 V ≤ EV _{DD0} ≤ 5.5 V		0.6		0.6		0.6		μs
Hold time when SCLA0 = "L"	t _{LOW}	2.7 V ≤ EV _{DD0} ≤ 5.5 V		1.3		1.3		1.3		μs
		1.8 V ≤ EV _{DD0} ≤ 5.5 V		1.3		1.3		1.3		μs
Hold time when SCLA0 = "H"	t _{HIGH}	2.7 V ≤ EV _{DD0} ≤ 5.5 V		0.6		0.6		0.6		μs
		1.8 V ≤ EV _{DD0} ≤ 5.5 V		0.6		0.6		0.6		μs
Data setup time (reception)	t _{SU:DAT}	2.7 V ≤ EV _{DD0} ≤ 5.5 V		100		100		100		μs
		1.8 V ≤ EV _{DD0} ≤ 5.5 V		100		100		100		μs
Data hold time (transmission) ^{Note 2}	t _{HD:DAT}	2.7 V ≤ EV _{DD0} ≤ 5.5 V		0	0.9	0	0.9	0	0.9	μs
		1.8 V ≤ EV _{DD0} ≤ 5.5 V		0	0.9	0	0.9	0	0.9	μs
Setup time of stop condition	t _{SU:STO}	2.7 V ≤ EV _{DD0} ≤ 5.5 V		0.6		0.6		0.6		μs
		1.8 V ≤ EV _{DD0} ≤ 5.5 V		0.6		0.6		0.6		μs
Bus-free time	t _{BUF}	2.7 V ≤ EV _{DD0} ≤ 5.5 V		1.3		1.3		1.3		μs
		1.8 V ≤ EV _{DD0} ≤ 5.5 V		1.3		1.3		1.3		μs

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.2. The maximum value (MAX.) of t_{HD:DAT} is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.**Caution** The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (I_{OH1}, I_{OL1}, V_{OH1}, V_{OL1}) must satisfy the values in the redirect destination.**Remark** The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.Fast mode: C_b = 320 pF, R_b = 1.1 kΩ

<R>

6. Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{ADC} when the A/D converter is in operation.
7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of I_{DD1} , I_{DD2} or I_{DD3} and I_{LVD} when the LVD circuit is in operation.
8. Current flowing only during data flash rewrite.
9. Current flowing only during self programming.
10. For shift time to the SNOOZE mode, see **18.3.3 SNOOZE mode** in the RL78/G13 User's Manual.

- Remarks**
1. f_{IL} : Low-speed on-chip oscillator clock frequency
 2. f_{SUB} : Subsystem clock frequency (XT1 clock oscillation frequency)
 3. f_{CLK} : CPU/peripheral hardware clock frequency
 4. Temperature condition of the TYP. value is $T_A = 25^{\circ}\text{C}$

(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)

 $(T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$, $\text{V}_{\text{SS}} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0\text{ V})$

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit		
			MIN.	MAX.			
Transfer rate		Transmission	4.0 V ≤ EV _{DD0} ≤ 5.5 V,			Note 1	bps
			2.7 V ≤ V _b ≤ 4.0 V			2.6 ^{Note 2}	Mbps
		2.7 V ≤ EV _{DD0} < 4.0 V,			Note 3	bps	
		2.3 V ≤ V _b ≤ 2.7 V			1.2 ^{Note 4}	Mbps	
		2.4 V ≤ EV _{DD0} < 3.3 V,			Note 5	bps	
		1.6 V ≤ V _b ≤ 2.0 V			0.43 ^{Note 6}	Mbps	

Notes 1. The smaller maximum transfer rate derived by using $f_{\text{MCK}}/12$ or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when $4.0\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$ and $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

- This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.
- The smaller maximum transfer rate derived by using $f_{\text{MCK}}/12$ or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when $2.7\text{ V} \leq \text{EV}_{\text{DD0}} < 4.0\text{ V}$ and $2.4\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

- This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.

(2) When reference voltage (+) = $AV_{REFP}/ANI0$ ($ADREFP1 = 0$, $ADREFP0 = 1$), reference voltage (–) = $AV_{REFM}/ANI1$ ($ADREFM = 1$), target pin : ANI16 to ANI26

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5\text{ V}$, $2.4\text{ V} \leq AV_{REFP} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0\text{ V}$, Reference voltage (+) = AV_{REFP} , Reference voltage (–) = $AV_{REFM} = 0\text{ V}$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES		8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution $EV_{DD0} \leq AV_{REFP} = V_{DD}$ Notes 3, 4	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$	1.2	± 5.0	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin : ANI16 to ANI26	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.125	39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.1875	39	μs
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17	39	μs
Zero-scale error ^{Notes 1, 2}	E_{ZS}	10-bit resolution $EV_{DD0} \leq AV_{REFP} = V_{DD}$ Notes 3, 4	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$		± 0.35	%FSR
Full-scale error ^{Notes 1, 2}	E_{FS}	10-bit resolution $EV_{DD0} \leq AV_{REFP} = V_{DD}$ Notes 3, 4	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$		± 0.35	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution $EV_{DD0} \leq AV_{REFP} = V_{DD}$ Notes 3, 4	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$		± 3.5	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution $EV_{DD0} \leq AV_{REFP} = V_{DD}$ Notes 3, 4	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$		± 2.0	LSB
Analog input voltage	V_{AIN}	ANI16 to ANI26	0		AV_{REFP} and EV_{DD0}	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when $AV_{REFP} = V_{DD}$.

Integral linearity error/ Differential linearity error: Add ± 0.5 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

4. When $AV_{REFP} < EV_{DD0} \leq V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 4.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

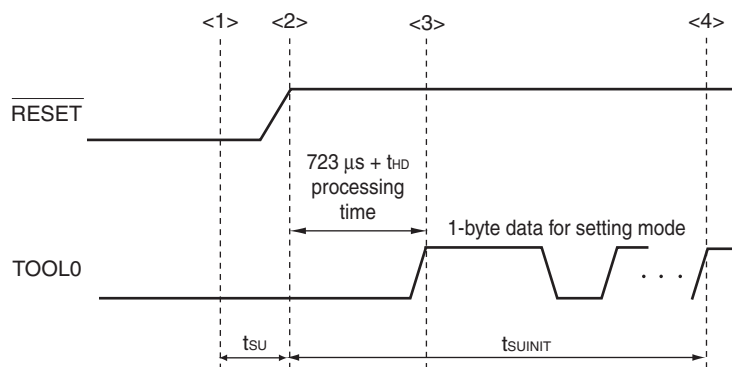
Zero-scale error/Full-scale error: Add $\pm 0.20\%$ FSR to the MAX. value when $AV_{REFP} = V_{DD}$.

Integral linearity error/ Differential linearity error: Add ± 2.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

3.10 Timing of Entry to Flash Memory Programming Modes

(T_A = -40 to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$, $\text{V}_{\text{SS}} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0\text{ V}$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	t_{SUNIT}	POR and LVD reset must be released before the external reset is released.			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	t_{SU}	POR and LVD reset must be released before the external reset is released.	10			μs
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	t_{HD}	POR and LVD reset must be released before the external reset is released.	1			ms



<1> The low level is input to the TOOL0 pin.

<2> The external reset is released (POR and LVD reset must be released before the external reset is released.).

<3> The TOOL0 pin is set to the high level.

<4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark t_{SUNIT} : Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.

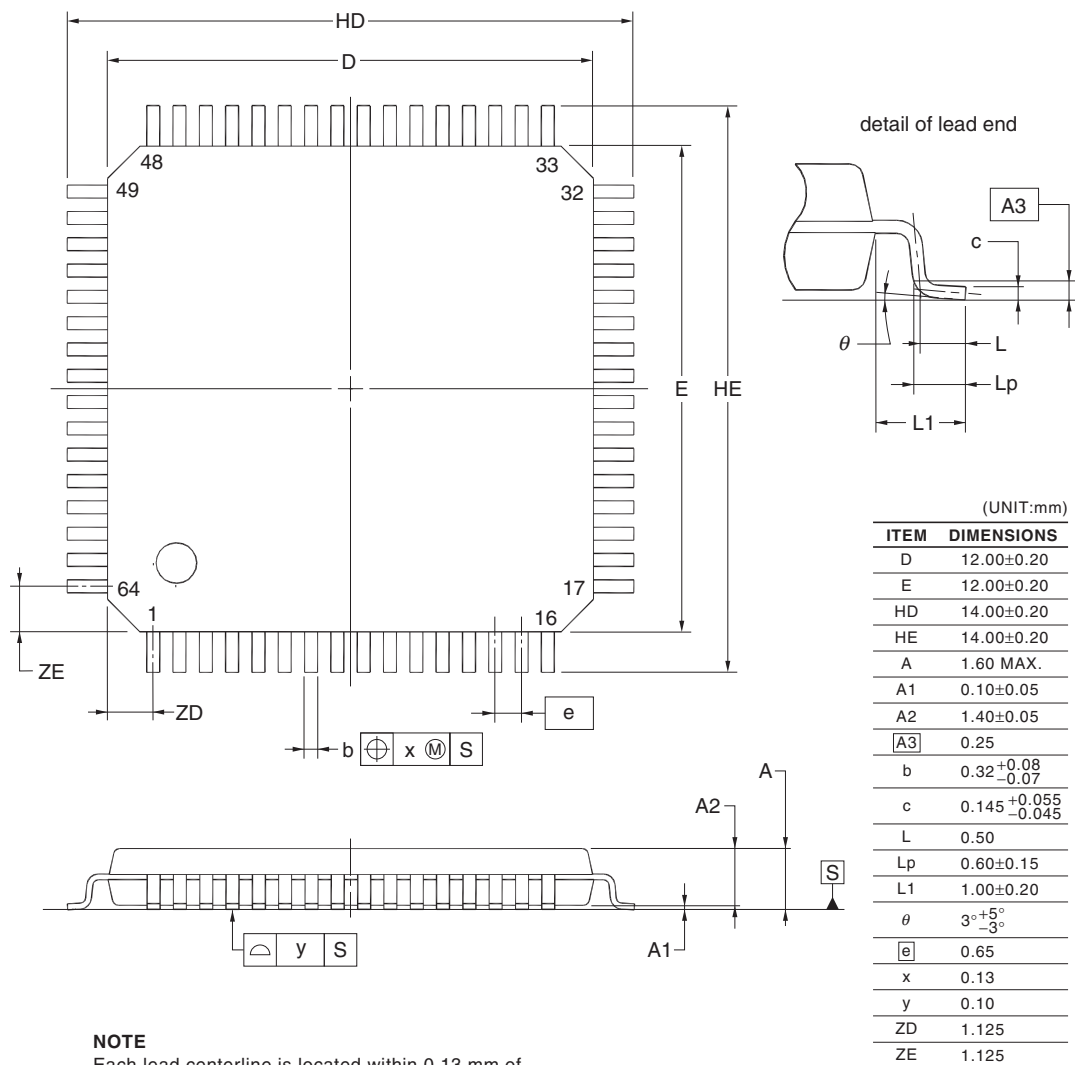
t_{SU} : Time to release the external reset after the TOOL0 pin is set to the low level

t_{HD} : Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)

4.11 64-pin Products

R5F100LCAFA, R5F100LDAFA, R5F100LEAFA, R5F100LFAFA, R5F100LGAFA, R5F100LHAFA, R5F100LJAF, A,
 R5F100LKAFA, R5F100LLAFA
 R5F101LCAFA, R5F101LDAFA, R5F101LEAFA, R5F101LFAFA, R5F101LGAFA, R5F101LHAFA, R5F101LJAF, A,
 R5F101LKAFA, R5F101LLAFA
 R5F100LCDFA, R5F100LDDFA, R5F100LEDFA, R5F100LFDFA, R5F100LG DFA, R5F100LHDFA, R5F100LJDFA,
 R5F100LK DFA, R5F100LLDFA
 R5F101LCDFA, R5F101LDDFA, R5F101LEDFA, R5F101LFDFA, R5F101LG DFA, R5F101LHDFA, R5F101LJDFA,
 R5F101LK DFA, R5F101LLDFA
 R5F100LCGFA, R5F100LDGFA, R5F100LEGFA, R5F100LFGFA, R5F100LGGFA, R5F100LHGFA,
 R5F100LJGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP64-12x12-0.65	PLQP0064JA-A	P64GK-65-UET-2	0.51



Rev.	Date	Description	
		Page	Summary
3.00	Aug 02, 2013	163	Modification of table in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I ² C mode) (1/2)
		164, 165	Modification of table, note 1, and caution in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I ² C mode) (2/2)
		166	Modification of table in 3.5.2 Serial interface IICA
		166	Modification of IICA serial transfer timing
		167	Addition of table in 3.6.1 A/D converter characteristics
		167, 168	Modification of table and notes 3 and 4 in 3.6.1 (1)
		169	Modification of description in 3.6.1 (2)
		170	Modification of description and note 3 in 3.6.1 (3)
		171	Modification of description and notes 3 and 4 in 3.6.1 (4)
		172	Modification of table and note in 3.6.3 POR circuit characteristics
		173	Modification of table of LVD Detection Voltage of Interrupt & Reset Mode
		173	Modification from Supply Voltage Rise Time to 3.6.5 Power supply voltage rising slope characteristics
		174	Modification of 3.9 Dedicated Flash Memory Programmer Communication (UART)
		175	Modification of table, figure, and remark in 3.10 Timing Specs for Switching Flash Memory Programming Modes
3.10	Nov 15, 2013	123	Caution 4 added.
		125	Note for operating ambient temperature in 3.1 Absolute Maximum Ratings deleted.
3.30	Mar 31, 2016		Modification of the position of the index mark in 25-pin plastic WFLGA (3 × 3 mm, 0.50 mm pitch) of 1.3.3 25-pin products
			Modification of power supply voltage in 1.6 Outline of Functions [20-pin, 24-pin, 25-pin, 30-pin, 32-pin, 36-pin products]
			Modification of power supply voltage in 1.6 Outline of Functions [40-pin, 44-pin, 48-pin, 52-pin, 64-pin products]
			Modification of power supply voltage in 1.6 Outline of Functions [80-pin, 100-pin, 128-pin products]
			$\overline{\text{ACK}}$ corrected to ACK
			$\overline{\text{ACK}}$ corrected to ACK

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